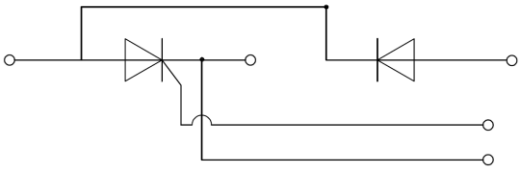
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FIG.1: Power dissipation vs. on-state current (per thyristor or diode)

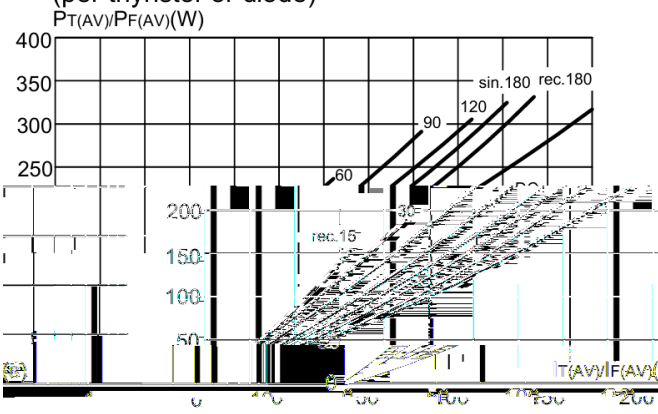


FIG.2: Maximum transient thermal impedance junction to case(per thyristor or diode)

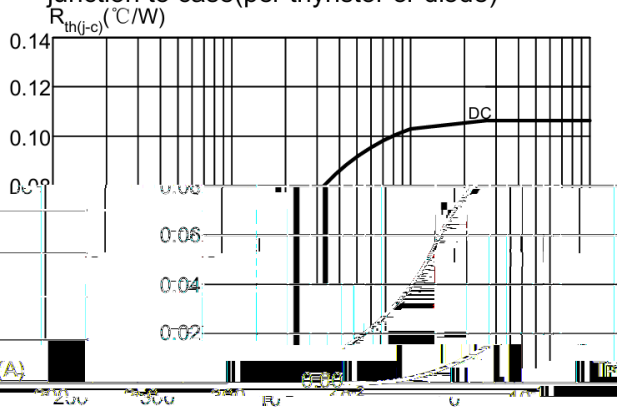


FIG.3: Forward characteristics (per thyristor or diode)

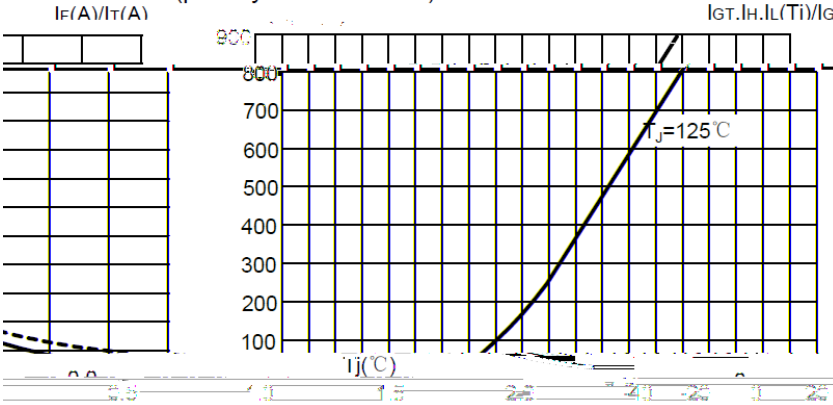
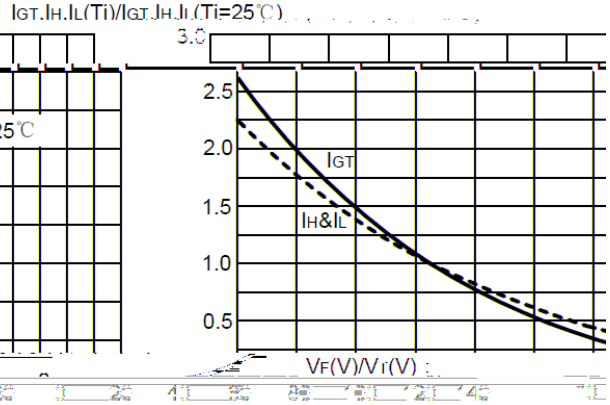
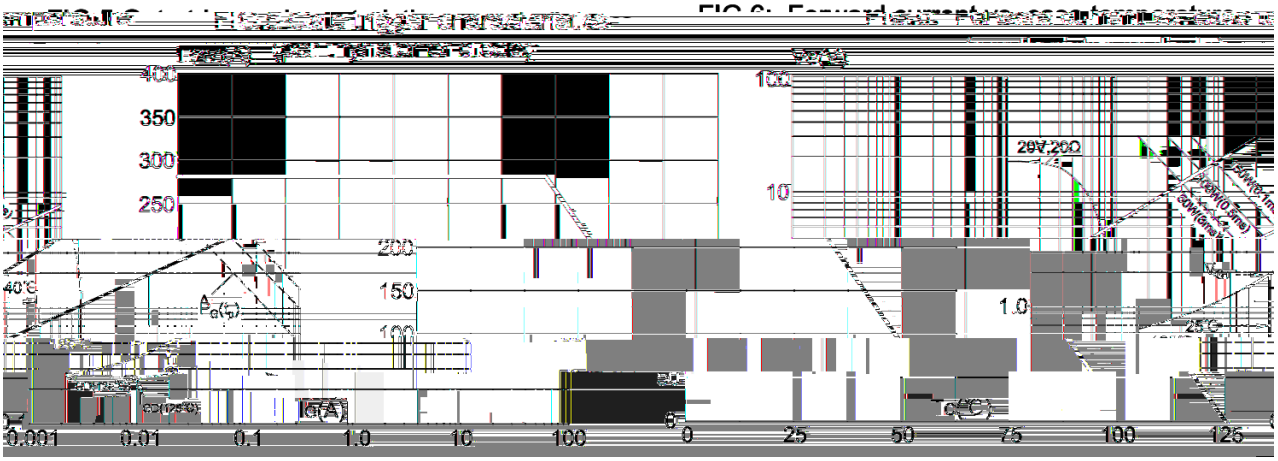
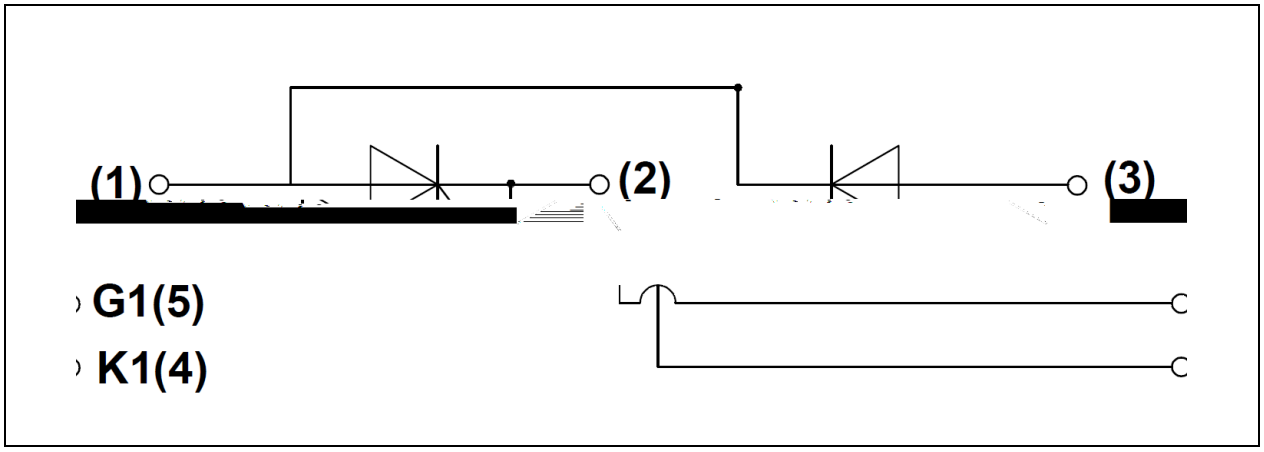
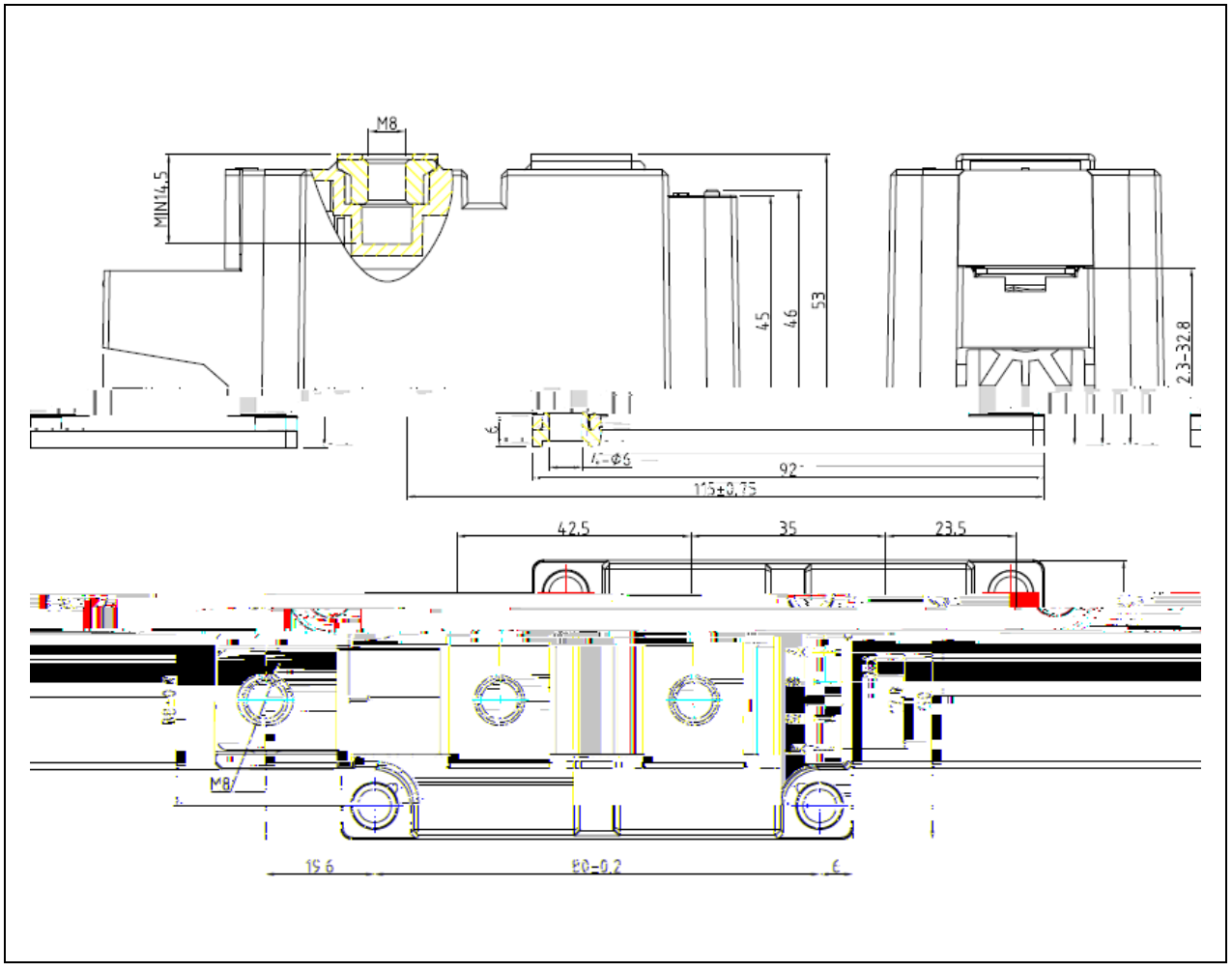


FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature






(1)
(2)
(3)
G1(5)
K1(4)


M8
MIN14.5
45
46
53
23-32.8
4-Φ6
92
115±0.75
42.5
35
23.5
M8
15.6
80-0.2
6